

FEATURES

Complimentary to PXT8550

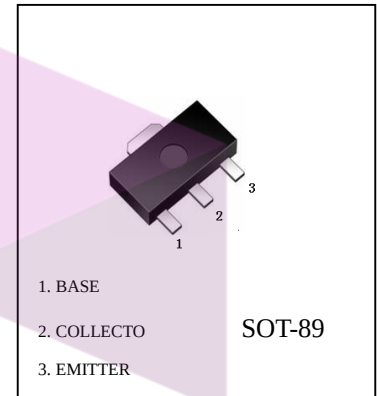
Collector current: $I_C=1.5A$

MARKING: Y1

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55-150	$^{\circ}C$

PXT8050 (NPN)



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20V, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	85		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=10mA$			1	V
Base-emitter positive forward voltage	V_{BEF}	$I_B=1A$			1.55	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA, f=30MHz$	100			MHz
output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			15	pF

CLASSIFICATION OF HFE

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

PXT8050 Typical Characteristics

